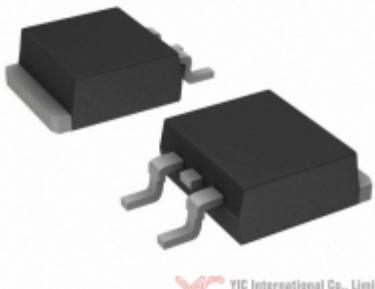








	<h2 style="color: #E67E22;">FQB19N10LTM</h2>
 <p>Image may be representation. See specs for product details.</p>	<b>Hersteller-Teilenummer:</b> <a href="#">FQB19N10LTM</a>
	<b>Hersteller / Marke:</b> <a href="#">Fairchild/ON Semiconductor</a>
	<b>Teil der Beschreibung:</b> MOSFET N-CH 100V 19A D2PAK
	<b>Datenblätter:</b>  <a href="#">FQB19N10LTM.pdf</a>
	<b>RoHs Status:</b> Bleifrei / RoHS-konform
	<b>Lagerzustand:</b> New original, 32363 pcs Stock Available.
<b>Liefern von:</b> Hong Kong	
<b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS	

### Spezifikationen

Teilenummer	<a href="#">FQB19N10LTM</a>
Hersteller	<a href="#">Fairchild/ON Semiconductor</a>
Beschreibung	MOSFET N-CH 100V 19A D2PAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	32363 pcs Stock
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D <sup>2</sup> Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D <sup>2</sup> PAK (TO-263AB)
Verlustleistung (max)	3.75W (Ta), 75W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (V <sub>dss</sub> )	100V
Strom - Ununterbrochener Abfluss (I <sub>d</sub> ) bei 25 ° C	19A (Tc)
R <sub>ds</sub> On (Max) @ I <sub>d</sub> , V <sub>gs</sub>	100 mOhm @ 9.5A, 10V
V <sub>GS</sub> (th) (Max) @ I <sub>d</sub>	2V @ 250µA
Gate Charge (Q <sub>g</sub> ) (Max) @ V <sub>gs</sub>	18nC @ 5V
Eingabekapazität (C <sub>iss</sub> ) (Max) @ V <sub>ds</sub>	870pF @ 25V
Verpackung	Tape & Reel (TR)

FQB19N10LTM ist neu im Original, Suche FQB19N10LTM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB19N10LTM Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB19N10LTM: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <b>FQB19N20C</b> F FQB19N20C F	 <b>FQB19N10TM</b> Fairchild/ON Semiconductor MOSFET N-CH 100V 19A D2PAK	 <b>FQB19N20</b> F FQB19N20 F	 <b>FQB19N10</b> FSC FSC TO-263
 <b>FQB17P10</b> FSC FQB17P10 FSC	 <b>FQB19N10LTM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 19A D2PAK	 <b>FQB19N10L</b> Fairchild/ON Semiconductor FQB19N10L FAIRCHILD	 <b>FQB17P10TM</b> AMI Semiconductor / ON Semiconductor MOSFET P-CH 100V 16.5A D2PAK

### heiße Teile

Mehr

<a href="#">FQB12N60TM_AM002</a>	<a href="#">FQB12N60TM_AM002</a>	<a href="#">FQB12P10</a>	<a href="#">FQB12P10TM</a>	<a href="#">FQB12P10TM</a>
<a href="#">FQB12P20</a>	<a href="#">FQB12P20TM</a>	<a href="#">FQB12P20TM</a>	<a href="#">FQB13N06L</a>	<a href="#">FQB13N10</a>
<a href="#">FQB13N10L</a>	<a href="#">FQB13N50</a>	<a href="#">FQB13N50CTM</a>	<a href="#">FQB13N50CTM</a>	<a href="#">FQB140N03L</a>
<a href="#">FQB14N30TM</a>	<a href="#">FQB14N30TM</a>	<a href="#">FQB16N25TM</a>	<a href="#">FQB16N25TM</a>	<a href="#">FQB17P06</a>
<a href="#">FQB17P10</a>	<a href="#">FQB17P10TM</a>	<a href="#">FQB17P10TM</a>	<a href="#">FQB19N10L</a>	<a href="#">FQB19N10LTM</a>
<a href="#">FQB19N10TM</a>	<a href="#">FQB19N10TM</a>	<a href="#">FQB19N20</a>	<a href="#">FQB19N20C</a>	<a href="#">FQB19N20CTM</a>
<a href="#">FQB19N20CTM</a>	<a href="#">FQB19N20L</a>	<a href="#">FQB19N20LTM</a>	<a href="#">FQB19N20LTM</a>	<a href="#">FQB19N20TM</a>
<a href="#">FQB19N20TM</a>	<a href="#">FQB1N60TM</a>	<a href="#">FQB1N60TM</a>	<a href="#">FQB20N06L</a>	<a href="#">FQB20N60FTM</a>
<a href="#">FQB20N60TM</a>	<a href="#">FQB22P10</a>	<a href="#">FQB22P10TM</a>	<a href="#">FQB22P10TM</a>	<a href="#">FQB22P10TM_F085</a>
<a href="#">FQB24N08TM</a>	<a href="#">FQB24N08TM</a>	<a href="#">FQB25N33</a>	<a href="#">FQB25N33TM</a>	<a href="#">FQB25N33TM</a>

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